

**AMENDMENT TO THE CLAIMS**

Please **AMEND** claims 17, 18, 32, 33 and 36 as follows.

Please **CANCEL** claim 14-16, 20, 22, 24-26, 31 and 35

A copy of all pending claims and a status of the claims are provided below.

Claims 1-16. (Canceled)

17. (currently amended) ~~A semiconductor structure according to claim 16;~~ A semiconductor structure comprising;  
a semiconductor substrate;  
a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and  
a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen, wherein  
the second gate dielectric is thicker than the first gate dielectric,  
the first gate dielectric has a first thickness susceptible to appreciable dopant diffusion and current leakage, and  
the second gate dielectric has a second thickness susceptible to appreciable dopant diffusion and current leakage,  
the second concentration of nitrogen is less than the first concentration of nitrogen, and  
the second active device is a p-channel field effect transistor and the first active device is an n-channel field effect transistor.

18. (currently amended) ~~A semiconductor structure according to claim 14;~~ A semiconductor structure comprising;

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen, wherein

the second gate dielectric is thicker than the first gate dielectric, and

the first gate dielectric has a first thickness being susceptible to appreciable dopant diffusion or current leakage; and the second gate dielectric having a second thickness not being susceptible to appreciable dopant diffusion or current leakage.

19. (Previously Presented) A semiconductor structure according to claim 18, wherein the second concentration of nitrogen is less than the first concentration of nitrogen.

20. (canceled)

21. (Original) A semiconductor structure according to claim 18, wherein the first thickness is less than about fifty angstroms; and the second thickness is about fifty angstroms or greater.

22. (canceled)

23. (Previously presented) A semiconductor structure comprising:

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen,

wherein the first concentration of nitrogen is about  $8 \times 10^{14}$  to  $1 \times 10^{22}$  atoms/cm<sup>3</sup>.

24-31. (canceled)

32. (currently amended) ~~The semiconductor structure of claim 31, A~~  
semiconductor structure comprising:

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen, wherein

the second gate dielectric is thicker than the first gate dielectric,

the first gate dielectric has a first thickness and the second gate dielectric has a second thickness greater than the first thickness, and the second concentration of nitrogen is less than the first concentration of nitrogen, and

the first active device is a p-well and the second active device is an n-well.

33. (currently amended) ~~The semiconductor structure of claim 31, A~~  
semiconductor structure comprising:

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen, wherein

the second gate dielectric is thicker than the first gate dielectric,

the first gate dielectric has a first thickness and the second gate dielectric has a second thickness greater than the first thickness, and wherein the second concentration of nitrogen is less than the first concentration of nitrogen, and

the first active device is a n-FET and the second active device is an p-FET.

34. (Previously Presented) The semiconductor structure of claim 33, wherein the first and second gate dielectrics are each an oxynitride layer.

35. (canceled)

36. (currently amended) ~~The semiconductor structure of claim 35, A~~  
semiconductor structure comprising:

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first gate dielectric, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second gate dielectric, which has a second concentration of nitrogen different than the first concentration of nitrogen, wherein

the second gate dielectric is thicker than the first gate dielectric,

the first gate dielectric has a first thickness and the second gate dielectric has a second thickness greater than the first thickness, and wherein the second concentration of nitrogen is less than the first concentration of nitrogen,

the first and second gate dielectrics are each an oxynitride layer, and

the first active device is a p-well or an n-FET and the second active device is an n-well or a p-FET.